

Pb RoHS

TSM35N10CP

100V N-Channel Power MOSFET

TO-252 (DPAK)

65

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

PRODUCT SUMMARY

V _{DS} (V)		$R_{DS(on)}(m\Omega)$	I _D (A)	
10	00	37 @ V _{GS} =10V	32	

Features

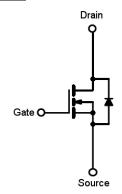
- Advanced Trench Technology
- Low $R_{DS(ON)} 37m\Omega$ (Max.)
- Low gate charge typical @ 34nC (Typ.)
- Low Crss typical @ 45pF (Typ.)

Ordering Information

Ordering code	Package	Packing
TSM35N10CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	±20	V		
	T _C =25°C		32	1	
Continuous Dunin Comment	T _C =70°C] ,	26	Α	
Continuous Drain Current	T _A =25°C	- I _D	5		
	T _A =70°C		4		
Drain Current-Pulsed Note 1		I _{DM}	70	Α	
Avalanche Current, L=0.1mH		I _{AS} , I _{AR}	35	Α	
Avalanche Energy, L=0.1mH		E _{AS} , E _{AR}	61	mJ	
	T _C =25°C		83.3		
Maximum Dawar Dissination	T _C =70°C		53.3	W	
Maximum Power Dissipation	T _A =25°C	- P _D	2		
	T _A =70°C		1.3	İ	
Storage Temperature Range		T _{STG}	-55 to +150	ô	
Operating Junction Temperature Range		T _J	-55 to +150	°C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	1.5	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62	°C/W



100V N-Channel Power MOSFET



Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 10A$	R _{DS(ON)}		30	37	mΩ
	$V_{GS} = 4.5V, I_D = 10A$	R _{DS(ON)}		32	42	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1	2	3	V
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 50V, I_{D} = 10A,$ $V_{GS} = 10V$	Qg		34		nC
Gate-Source Charge		Q_{gs}		6		
Gate-Drain Charge		Q_{gd}		9		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{iss}		1598		
Output Capacitance		C _{oss}		132		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		45		
Switching						
Turn-On Delay Time		t _{d(on)}		7		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 50V,$	t _r		7		
Turn-Off Delay Time	$R_G = 3\Omega$	t _{d(off)}		29		nS
Turn-Off Fall Time		t _f		7		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}		0.7		V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		32		nS
Reverse Recovery Charge	dI/dt = 500A/us	Q_{fr}		200		nC

Notes:

1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

^{2.} R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. R_{eJC} is guaranteed by design while R_{eCA} is determined by the user's board design.

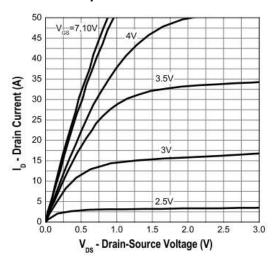


100V N-Channel Power MOSFET

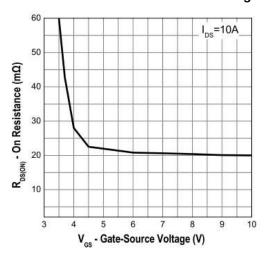


Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

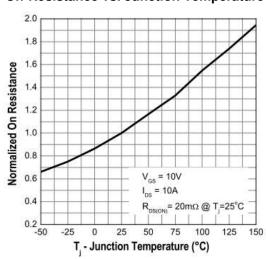
Output Characteristics



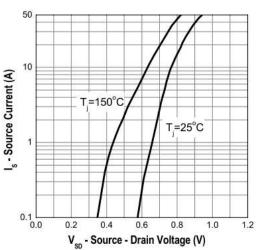
On-Resistance vs. Gate-Source Voltage



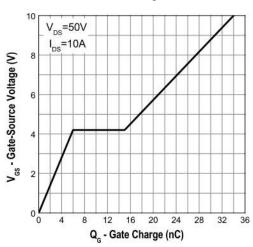
On-Resistance vs. Junction Temperature



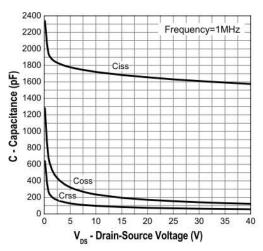
Transfer Characteristics



Gate Charge



Capacitance



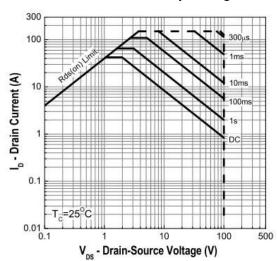


100V N-Channel Power MOSFET

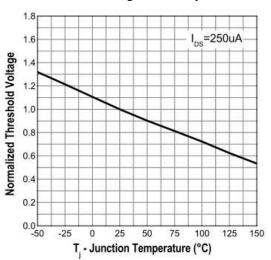


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

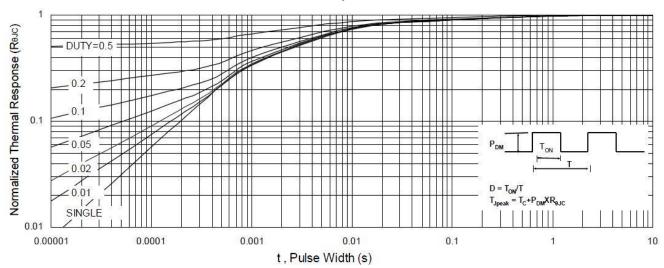
Maximum Safe Operating Area



Threshold Voltage vs. Temperature



Normalized Thermal Transient Impedance, Junction-to-Ambient



4/6

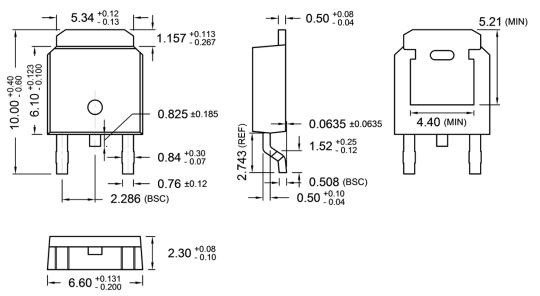
Version: C1807





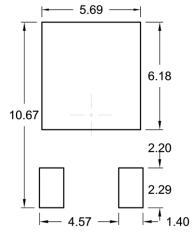


TO-252 Mechanical Drawing



Unit: Millimeters

SUGGESTED PAD LAYOUT (Unit: Millimeters)



Marking Diagram





TSM35N10CP 100V N-Channel Power MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.